

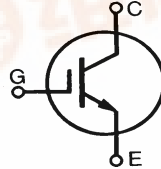
# IGBT High Speed

**IXSH 50N60B**

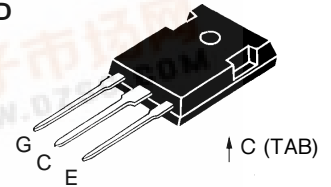
$V_{CES} = 600\text{ V}$   
 $I_{C25} = 75\text{ A}$   
 $V_{CE(sat)} = 2.5\text{ V}$

Short Circuit SOA Capability

Preliminary data sheet



Symbol	Test Conditions	Maximum Ratings	TO-247 AD
$V_{CES}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$	600	V
$V_{CGR}$	$T_J = 25^\circ\text{C}$ to $150^\circ\text{C}$ ; $R_{GE} = 1\text{ M}\Omega$	600	V
$V_{GES}$	Continuous	$\pm 20$	V
$V_{GEM}$	Transient	$\pm 30$	V
$I_{C25}$	$T_C = 25^\circ\text{C}$ , limited by leads	75	A
$I_{C90}$	$T_C = 90^\circ\text{C}$	50	A
$I_{CM}$	$T_C = 25^\circ\text{C}$ , 1 ms	200	A
<b>SSOA (RBSOA)</b>	$V_{GE} = 15\text{ V}$ , $T_{VJ} = 125^\circ\text{C}$ , $R_G = 22\ \Omega$ Clamped inductive load, $L = 30\ \mu\text{H}$	$I_{CM} = 100$ @ $0.8 V_{CES}$	A
<b><math>t_{SC}</math> (SCSOA)</b>	$V_{GE} = 15\text{ V}$ , $V_{CE} = 360\text{ V}$ , $T_J = 125^\circ\text{C}$ $R_G = 22\ \Omega$ , non repetitive	10	$\mu\text{s}$
$P_C$	$T_C = 25^\circ\text{C}$	250	W
$T_J$		-55 ... +150	$^\circ\text{C}$
$T_{JM}$		150	$^\circ\text{C}$
$T_{stg}$		-55 ... +150	$^\circ\text{C}$
$M_d$	Mounting torque	1.13/10	Nm/lb.in.
<b>Weight</b>		TO-247 SMD 4	g
		TO-247 6	g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$



G = Gate, C = Collector,  
E = Emitter, TAB = Collector

### Features

- International standard package JEDEC TO-247 AD, and TO-247 SMD for surface mount
- Guaranteed Short Circuit SOA capability
- High frequency IGBT
- Latest generation HDMOS™ process
- Low  $V_{CE(sat)}$  - for minimum on-state conduction losses
- MOS Gate turn-on - drive simplicity

### Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switch-mode and resonant-mode power supplies

### Advantages

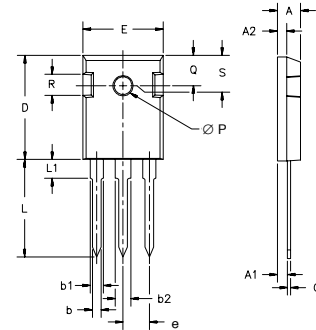
- Easy to mount with 1 screw (isolated mounting screw hole)
- Reduces assembly time and cost
- High power density

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)		
		min.	typ.	max.
$BV_{CES}$	$I_C = 250\ \mu\text{A}$ , $V_{GE} = 0\text{ V}$	600		V
$V_{GE(th)}$	$I_C = 4\text{ mA}$ , $V_{CE} = V_{GE}$	4		8 V
$I_{CES}$	$V_{CE} = 0.8 \cdot V_{CES}$ , $T_J = 25^\circ\text{C}$ $V_{GE} = 0\text{ V}$ , $T_J = 125^\circ\text{C}$			200 $\mu\text{A}$ 1 mA
$I_{GES}$	$V_{CE} = 0\text{ V}$ , $V_{GE} = \pm 20\text{ V}$			$\pm 100\text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$	2.2	2.5	V



Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$I_C = I_{C90}$ ; $V_{CE} = 10\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $\leq 2\%$	16	23	S	
$I_{C(on)}$	$V_{GE} = 15\text{ V}$ , $V_{CE} = 10\text{ V}$		160	A	
$C_{ies}$	$V_{CE} = 25\text{ V}$ , $V_{GE} = 0\text{ V}$ , $f = 1\text{ MHz}$		3850	pF	
$C_{oes}$			440	pF	
$C_{res}$			50	pF	
$Q_g$	$I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $V_{CE} = 0.5 V_{CES}$		167	nC	
$Q_{ge}$			45	nC	
$Q_{gc}$			88	nC	
$t_{d(on)}$	<b>Inductive load, <math>T_J = 25^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		70	ns	
$t_{ri}$			70	ns	
$t_{d(off)}$			150	300	ns
$t_{fi}$			150	300	ns
$E_{off}$			3.3	6.0	mJ
$t_{d(on)}$	<b>Inductive load, <math>T_J = 125^\circ\text{C}</math></b> $I_C = I_{C90}$ , $V_{GE} = 15\text{ V}$ , $L = 100\ \mu\text{H}$ , $V_{CE} = 0.8 V_{CES}$ , $R_G = 2.7\ \Omega$ Remarks: Switching times may increase for $V_{CE}$ (Clamp) $> 0.8 \cdot V_{CES}$ , higher $T_J$ or increased $R_G$		70	ns	
$t_{ri}$			70	ns	
$E_{on}$			0.6	mJ	
$t_{d(off)}$			230	ns	
$t_{fi}$			230	ns	
$E_{off}$			4.8	mJ	
$R_{thJC}$			0.5	KW	
$R_{thCK}$		0.25		KW	

### TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
∅P	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

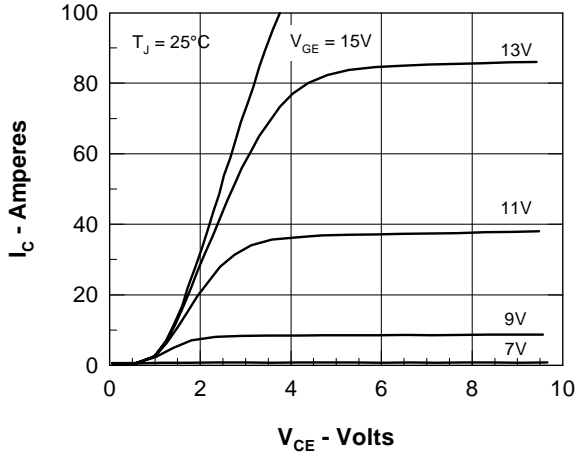


Figure 1. Saturation Voltage Characteristics

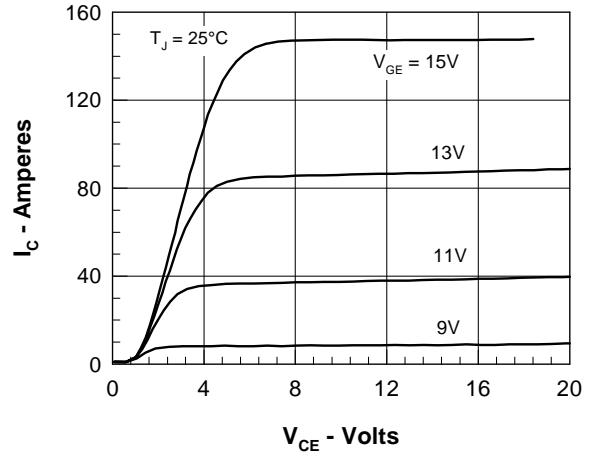


Figure 2. Extended Output Characteristics

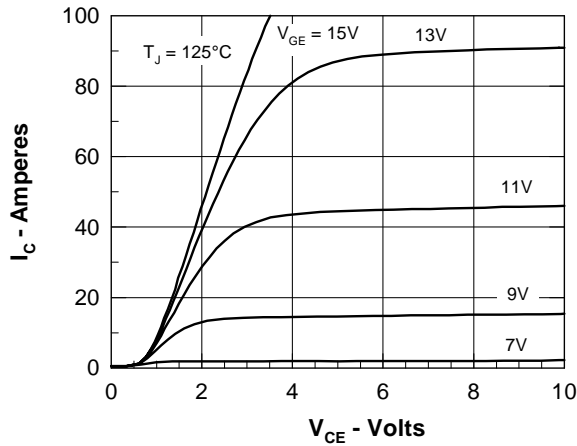


Figure 3. Saturation Voltage Characteristics

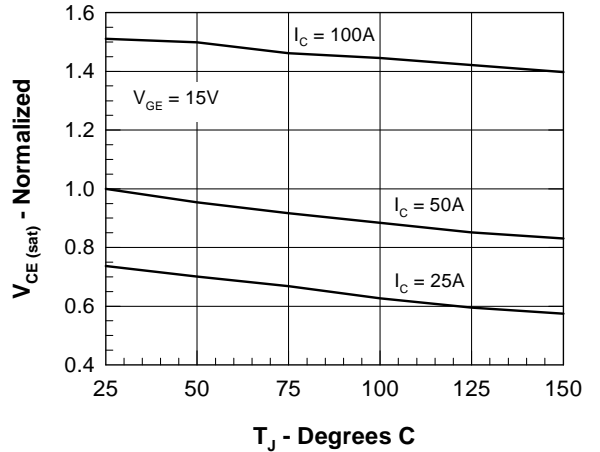


Figure 4. Temperature Dependence of  $V_{CE(sat)}$

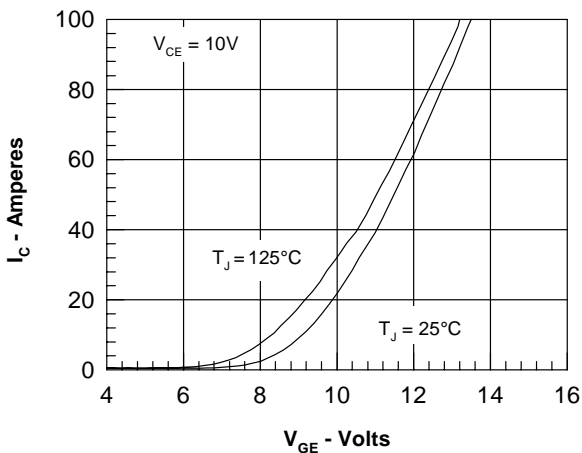


Figure 5. Admittance Curves

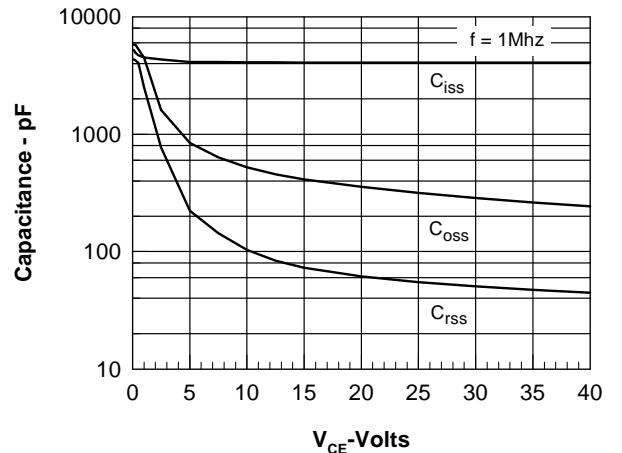


Figure 6. Capacitance Curves

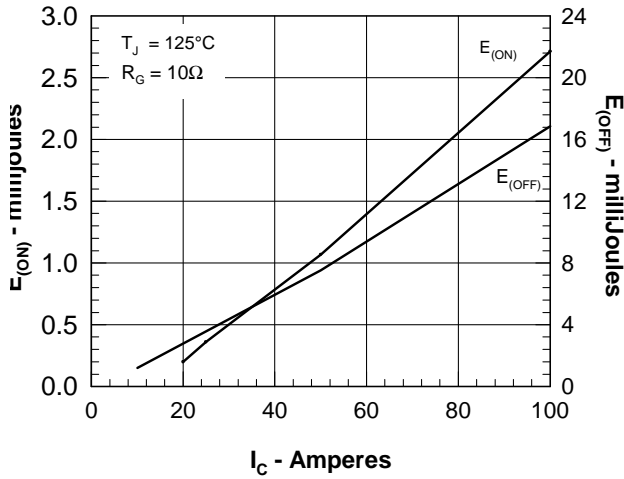


Figure 7. Dependence of  $E_{ON}$  and  $E_{OFF}$  on  $I_C$ .

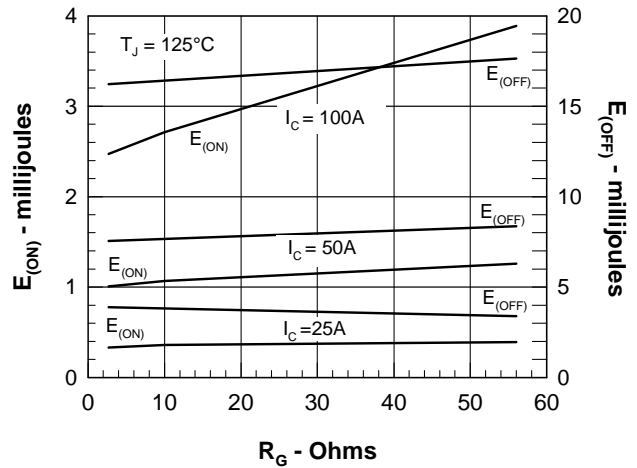


Figure 8. Dependence of  $E_{ON}$  and  $E_{OFF}$  on  $R_G$ .

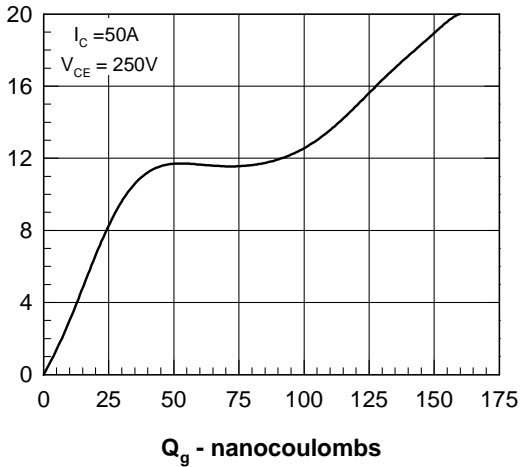


Figure 9. Gate Charge

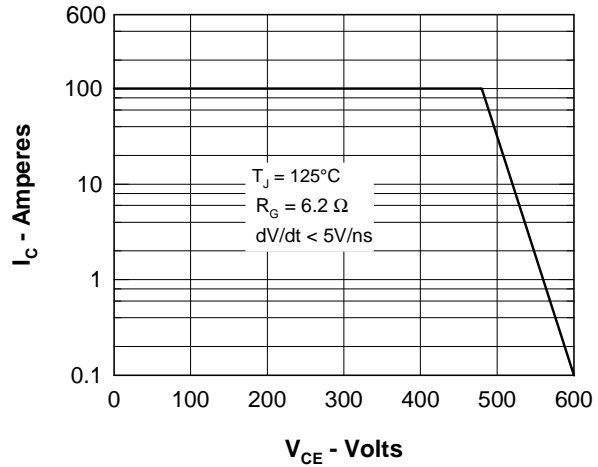


Figure 10. Turn-off Safe Operating Area

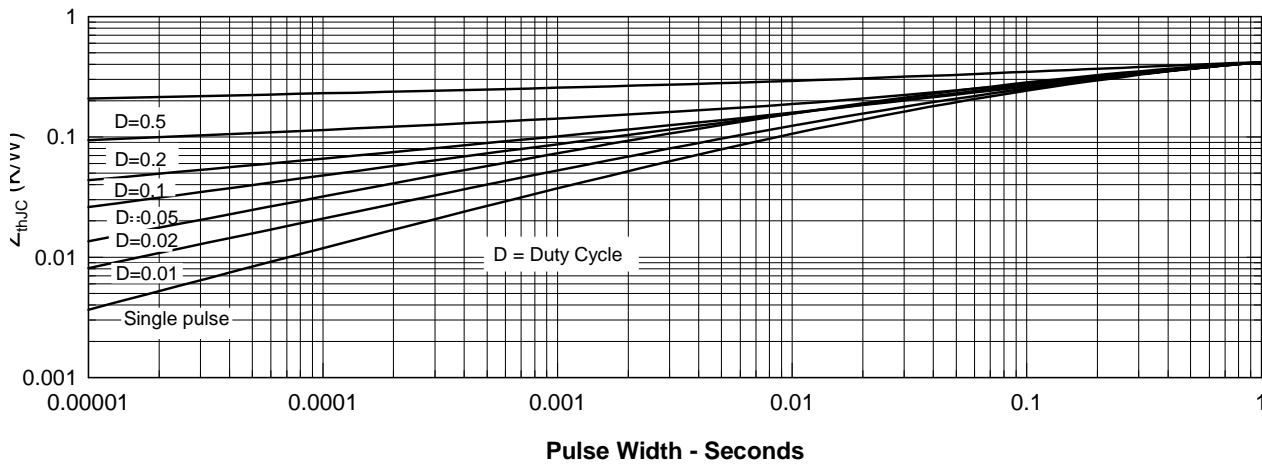


Figure 11. Transient Thermal Resistance